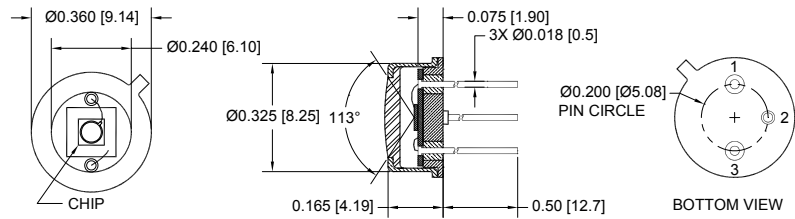
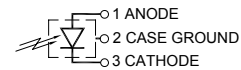
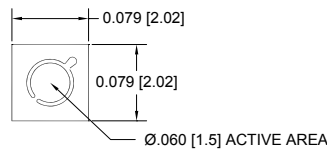




PACKAGE DIMENSIONS INCH [mm]



CHIP DIMENSIONS INCH [mm]



TO-39 PACKAGE

FEATURES

- Low noise
- Low dark current
- High response

DESCRIPTION

The **SD 060-11-41-211** is a InGaAs photodiode with high sensitivity and low noise characteristics packaged in a three leaded hermetic TO-39 metal package.

APPLICATIONS

- Communication
- Industrial
- Medical

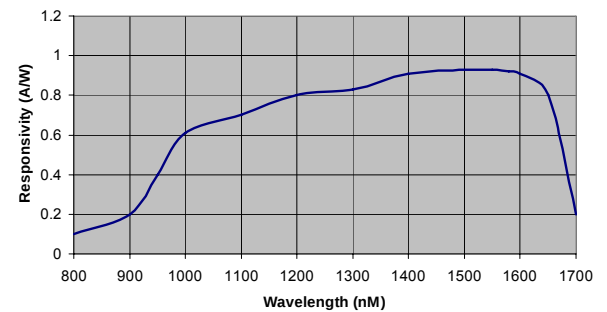


ABSOLUTE MAXIMUM RATING (TA) = 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_{BR}	Reverse Voltage		75	V
T_{STG}	Storage Temperature	-55	+100	°C
T_O	Operating Temperature	-40	+85	°C
T_S	Soldering Temperature*		+260	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA) = 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_D	Dark Current	$V_R = 5V$		10	50	nA
R_{SH}	Shunt Resistance	$V_R = 10 mV$	2	6		$M\Omega$
C_J	Junction Capacitance	$V_R = 5V, f = 1 MHz$		250	450	pF
λ_{range}	Spectral Application Range	Spot Scan	800		1700	nm
R	Responsivity	$\lambda = 1310nm, V_R = 5V$	0.83	0.92		A/W
V_{BR}	Breakdown Voltage	$I = 1\mu A$		18		V
NEP	Noise Equivalent Power	$V_R = 5V @ \lambda = 1310nm$		1.79×10^{-14}		$W/\sqrt{Hz}$
t_r	Response Time**	$RL = 50 \Omega, V_R = 5V$			10	nS

**Response time of 10% to 90% is specified at 1310nm wavelength light.

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